

NTE236 Silicon NPN Transistor Final RF Power Output (P_O = 16W, 27MHz, SSB) TO220AB

Description:

The NTE236 is a silicon NPN transistor in a TO220AB type package designed for 10–14 watt output power class AB amplifier applications in the HF band.

Features:

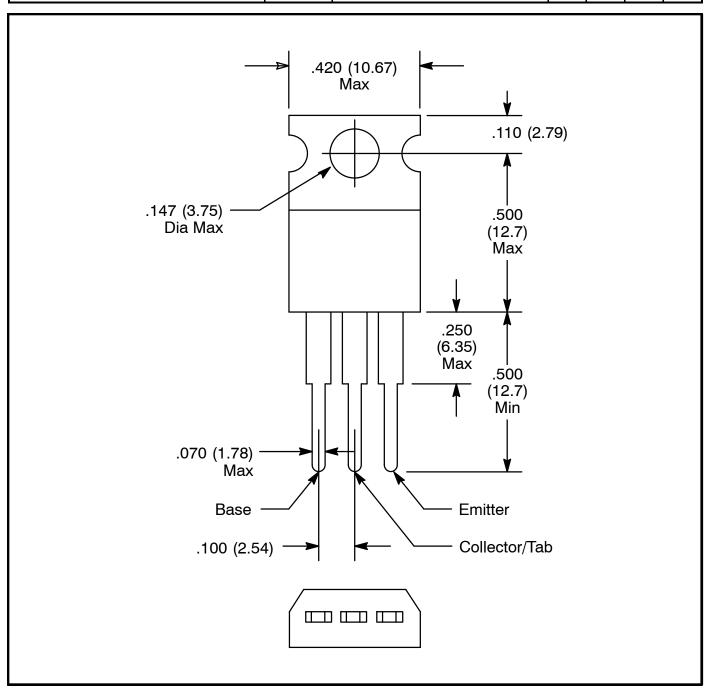
- High Power Gain: $G_{pe} \ge 12dB$, $P_O = 16W$, f = 27MHz
- High Reliability

Application:

10 to 14 Watt Output Power Class AB Amplifier Applications in the HF band

Electrical Characteristics: $(T_A = +25^{\circ}C \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	$I_E = 5mA, I_C = 0$	5	_	_	V
Collector-Base Breakdown Voltage	V _{(BR)CBO}	I _C = 1mA, I _E = 0	60	_	_	V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I_C = 10mA, R_{BE} = ∞	25	_	_	V
Collector Cutoff Current	I _{CBO}	$V_{CB} = 30V, I_{E} = 0$	_	_	0.1	mA
Emitter Cutoff Current	I _{EBO}	V _{EB} = 4V, I _C = 0	_	_	0.1	mA
DC Forward Current Gain	h _{FE}	V _{CE} = 12V, I _C = 10mA	90	_	180	_
Output Power	Po	V _{CC} = 12V, P _{in} = 1W, f = 27MHz	16	18	_	W
Collector Efficiency	h _C	V _{CC} = 12V, P _{in} = 1W, f = 27MHz	60	70	_	%



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